

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	1193	(427/562-564, 570, 575) .CCLS.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/06/0 6 13:37
2	L2	4454	(427/562-564, 569-579) .CCLS.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/06/0 6 13:37
3	L3	4035	(427/566-567, 250, 255. 31-255.38) .CCLS.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/06/0 6 13:41
4	L4	104	1 and 3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/06/0 6 13:42

SND 098,869

2

	L #	Hits	Search Text	DBs	Time Stamp
5	L5	370	2 and 3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/06 13:42
6	L6	266	5 not 4	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/06 13:44
7	L7	2175	(427/523-531).CCLS.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/06 13:45
8	L8	7348	(204/192.1-192.3,192.38).CCLS.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/06 13:47

3

	L #	Hits	Search Text	DBs	Time Stamp
9	L9	176	1 and (7 or 8)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB-	2003/06/06 13:48
10	L10	148	9 not 4	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB-	2003/06/06 13:49
11	L11	133776	(different\$4 differentiat\$4 gradient vary\$4) near pressure	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB-	2003/06/06 13:54
12	L12	9	4 and 11	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB-	2003/06/06 13:55

6/8/03
miss spelled
gradient
→

4

	L #	Hits	Search Text	DBs	Time Stamp
13	L13	95	4 not 12	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/06/0 6 13:54
14	L14	15	6 and 11	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/06/0 6 13:54
15	L15	251	6 not 14	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/06/0 6 13:55
16	L16	5	10 and 11	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/06/0 6 13:55

5

	L #	Hits	Search Text	DBs	Time Stamp
17	L17	143	10 not 16	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/0 6 13:55

L12

6

	Document ID	Issue Date	Title	Current OR	Inventor
1	US 5324553 A	19940628	Method for the improved microwave deposition of thin films	427/571	Ovshinsky, Stanford R. et al.
2	US 4859493 A	19890822	Methods of forming synthetic diamond coatings on particles using microwaves	427/562	Lemelson, Jerome H.
3	US 4812326 A	19890314	Evaporation source with a shaped nozzle	427/562	Tsukazaki, Hisashi et al.
4	US 4717584 A	19880105	Method of manufacturing a magnetic thin film	427/573	Aoki, Masaki et al.
5	US 4657776 A	19870414	CVD process for the production of a superconducting fiber bundle	427/570	Dietrich, Manfred et al.

7

	Document ID	Issue Date	Title	Current OR	Inventor
6	US 4609564 A <i>Fig 6 - vaporization chamber removing from deposition (col 8)</i>	19860902 <i>sub</i>	Method of and apparatus for the coating of a substrate with material electrically transformed into a vapor phase	427/580	Pinkhasov, Eduard
7	US 4438153 A	19840320	Method of and apparatus for the vapor deposition of material upon a substrate	427/564	Pinkhasov, Eduard
8	US 4351855 A	19820928	Noncrucible method of and apparatus for the vapor deposition of material upon a substrate using voltaic arc in vacuum	427/564	Pinkhasov, Eduard

	Document ID	Issue Date	Title	Current OR	Inventor
9	US 4197175 A <i>W/2</i>	1980040 8 <i>✓</i>	Method and apparatus for evaporating materials in a vacuum coating plant	204/192 .38	Moll, Eberhard et al.

L14

9

	Document ID	Issue Date	Title	Current OR	Inventor
1	US 6531193 B2	20030311	Low temperature, high quality silicon dioxide thin films deposited using tetramethylsilane (TMS) for stress control and coverage applications	427/579	Fonash, Stephen J. et al.
2	US 6491978 B1	20021210	Deposition of CVD layers for copper metallization using novel metal organic chemical vapor deposition (MOCVD) precursors	427/255.394	Kalyanam, Jagadish

	Document ID	Issue Date	Title	Current OR	Inventor
3	US 6177135 B1	20010123	Low temperature CVD processes for preparing ferroelectric films using Bi amides	427/255.31	Hintermaier, Frank S. et al.
4	US 6040022 A	20000321	PECVD of compounds of silicon from silane and nitrogen	427/579	Chang, Mei et al.
5	US 5989652 A	19991123	Method of low temperature plasma enhanced chemical vapor deposition of tin film over titanium for use in via level applications	427/534	Ameen, Michael S. et al.
6	US 5904952 A	19990518	Method of plasma enhanced silicon oxide deposition	427/8	Lopata, Eugene S. et al.

	Document ID	Issue Date	Title	Current OR	Inventor
7	US 5853815 A	19981229	Method of forming uniform thin coatings on large substrates	427/446	Muehlberger, Erich
8	US 5738917 A	19980414	Process for in-situ deposition of a Ti/TiN/Ti aluminum underlayer	427/576	Besser, Paul R. et al.
9	US 5582881 A	19961210	Process for deposition of a Ti/TiN cap layer on aluminum metallization and apparatus	427/576	Besser, Paul R. et al.
10	US 5368890 A	19941129	"Coating process for depositing extremely hard films on substrates"	427/249.8	de Nagybazon, Erno N.

	Document ID	Issue Date	Title	Current OR	Inventor
11	US 5338364 A	19940816	Process and apparatus for producing diamond film	118/729	Kurihara, Kazuaki et al.
12	US 5221561 A	19930622	Process for the photochemical treatment of a material using a flash tube light source	427/534	Flicstein, Jean et al.
13	US 5004721 A	19910402	As-deposited oxide superconductor films on silicon and aluminum oxide	505/477	DeLozanne, A. L.
14	US 4612207 A	19860916	Apparatus and process for the fabrication of large area thin film multilayers	427/576	Jansen, Frank

pull

Abs - Sub & evaporation in diff. chambers w/ pressure diff
US - direct & plasma
crystal growth

	Document ID	Issue Date	Title	Current OR	Inventor
15	US 4485125 A	1984112 7	Method for continu ously produci ng tandem amorpho us photovo ltaic cells	427/74	Izu, Masatsu gu et al.

L/6

14

	Document ID	Issue Date	Title	Current OR	Inventor
1	(DP) Input gas flows ... US 4943345 A	19900724	Plasma reactor apparatus and method for treating a substrate	216/69	Asmusse n, Jes et al.
2	US 4937094 A	19900626	Method of creating a high flux of activated species for reaction with a remotely located substrate	427/574	Doehler, Joachim et al.
3	US 4916091 A	19900410	Plasma and plasma UV deposition of SiO ₂ sub .2	438/784	Freeman, Dean W. et al.

different pressure
high pressure
low pressure
63

15

	Document ID	Issue Date	Title	Current OR	Inventor
4	US 4883686 A	19891128	Method for the high rate plasma deposition of high quality material	427/562	Doehler, Joachim et al.
5	US 3961103 A	19760601	Film deposition	427/523	Aisenberg, Sol